

# Pch 100V 13A Power MOSFET

$V_{DSS}$	-100V
R <sub>DS(on)</sub> (Max.)	200m $Ω$
I <sub>D</sub>	-13A
$P_D$	20W

### Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Drive circuits can be simple.
- 4) Parallel use is easy.
- 5) Pb-free lead plating; RoHS compliant
- 6) 100% Avalanche tested

## Application

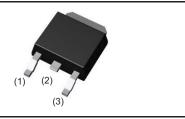
**Switching Power Supply** 

**Automotive Motor Drive** 

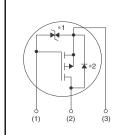
Automotive Solenoid Drive

### Outline

CPT3 (SC-63) <SOT-428>



## •Inner circuit



- (1) Gate
- (2) Drain
- (3) Source
- \*1 ESD PROTECTION DIODE
- \*2 BODY DIODE

Packaging specifications

	Packaging	Taping
	Reel size (mm)	330
Typo	Tape width (mm)	16
Туре	Basic ordering unit (pcs)	2,500
	Taping code	TL
	Marking	131P10

# ● **Absolute maximum ratings**(T<sub>a</sub> = 25°C)

Paramete	Symbol	Value	Unit	
Drain - Source voltage	V <sub>DSS</sub>	-100	V	
Continuous drain current	T <sub>c</sub> = 25°C	I <sub>D</sub> *1	±13	А
Continuous drain current	T <sub>c</sub> = 100°C	I <sub>D</sub> *1	±7.0	А
Pulsed drain current		I <sub>D,pulse</sub> *2	±52	А
Gate - Source voltage		V <sub>GSS</sub>	±20	V
Avalanche energy, single pulse		E <sub>AS</sub> *3	11.9	mJ
Avalanche current		I <sub>AR</sub> *3	-13	А
Dower dissination	T <sub>c</sub> = 25°C	P <sub>D</sub>	20	W
Power dissipation $T_a = 25^{\circ}C$		P <sub>D</sub>	0.85	W
Junction temperature		Tj	150	°C
Range of storage temperature	T <sub>stg</sub>	-55 to +150	°C	

## ●Thermal resistance

Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	$R_{thJC}$	-	-	6.25	°C/W

# •Electrical characteristics( $T_a = 25^{\circ}C$ )

Parameter	Symbol Conditions -		Values			Unit
- Farameter	Symbol	Conditions		Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$ , $I_D = -1mA$	-100	-	-	V
		$V_{DS} = -100V, V_{GS} = 0V$			1	
Zara gata valtaga drain aurrent		T <sub>j</sub> = 25°C	-	-	_1	μΑ
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = -100V, V_{GS} = 0V$			-100	
		T <sub>j</sub> = 125°C	-	-		
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μА
Gate threshold voltage	V <sub>GS (th)</sub>	$V_{DS} = -10V, I_{D} = -1mA$	-1	-	-2.5	V
		$V_{GS} = -10V, I_D = -6.5A$	-	135	200	
		$V_{GS} = -4.5V, I_D = -6.5A$	-	150	220	
Static drain - source on - state resistance	$R_{DS(on)}^{}^{*4}}$	$V_{GS} = -4.0V, I_D = -6.5A$	-	155	230	mΩ
		$V_{GS} = -10V, I_D = -13A$		250	250	1
		T <sub>j</sub> = 125°C	-	250	350	
Forward transfer admittance	9 <sub>fs</sub>	$V_{DS} = -10V, I_{D} = -13A$	10	20	-	S

# ●Electrical characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions		Unit		
r ai ai ii e lei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	2400	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -25V	-	100	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	65	-	
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq -50V, V_{GS} = -10V$	-	20	-	
Rise time	t <sub>r</sub> *4	$I_D = -6.5A$	-	25	-	no
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 7.68\Omega$	-	70	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 10\Omega$	-	60	-	

# ●Gate Charge characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions		Values		Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Qg *4	$V_{DD} \simeq -50V$	-	40	-	
Gate - Source charge	Q <sub>gs</sub> *4	I <sub>D</sub> = -13A	-	6	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4	$V_{GS} = -10V$	-	6	-	
Gate plateau voltage	V <sub>(plateau)</sub>	$V_{DD} \simeq -50V, I_D = -13A$	-	-3.2	-	V

# ●Body diode electrical characteristics (Source-Drain)(T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions		Unit		
- arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Continuous source current	l <sub>s</sub> *1	T <sub>c</sub> = 25°C	-	-	-13	Α
Pulsed source current	I <sub>SM</sub> *2	1 c = 20 C	ı	ı	-52	Α
Forward voltage	V <sub>SD</sub> *4	$V_{GS} = 0V, I_{S} = -13A$	ı	ı	-1.2	V
Reverse recovery time	t <sub>rr</sub> *4	I <sub>S</sub> = -13A	-	60	-	ns
Reverse recovery charge	Q <sub>rr</sub> *4	di/dt = -100A/μs	-	160	-	μС

<sup>\*1</sup> Limited only by maximum temperature allowed.

<sup>\*2</sup> Pw  $\leq$  10 $\mu$ s, Duty cycle  $\leq$  1%

<sup>\*3</sup> L  $\simeq$  100 $\mu$ H, V<sub>DD</sub> = -50V, Rg = 10 $\Omega$ , starting T<sub>j</sub> = 25°C

<sup>\*4</sup> Pulsed

Fig.1 Power Dissipation Derating Curve

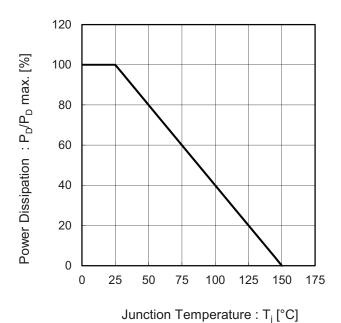
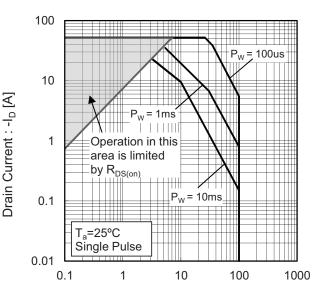
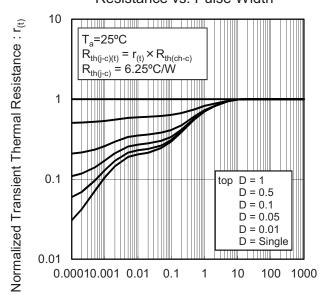


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width :  $P_W[s]$ 

Fig.4 Avalanche Current vs Inductive Load

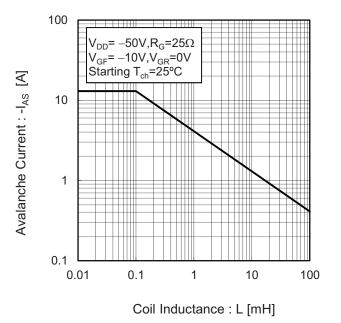
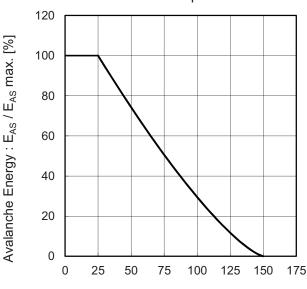
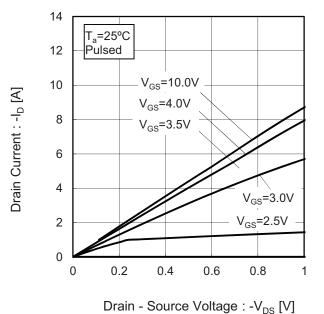


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature



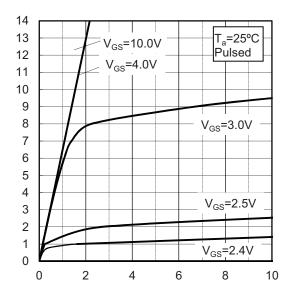
Junction Temperature : T<sub>i</sub> [°C]

Fig.6 Typical Output Characteristics(I)



Drain Current : -I<sub>D</sub> [A]

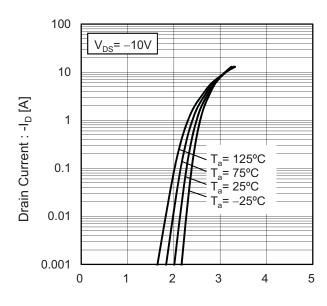
Fig.7 Typical Output Characteristics(II)



Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.8 Breakdown Voltage vs. Junction Temperature 120 Normarize Drain - Source Breakdown Voltage  $V_{GS} = 0V$  $I_D = -1mA$ 110 100 : -V<sub>(BR)DSS</sub> [V] 90 80 70 60 0 50 100 -50 150 Junction Temperature : T<sub>i</sub> [°C]

Fig.9 Typical Transfer Characteristics



Gate - Source Voltage :  $-V_{GS}[V]$ 

Fig.10 Gate Threshold Voltage vs. Junction Temperature

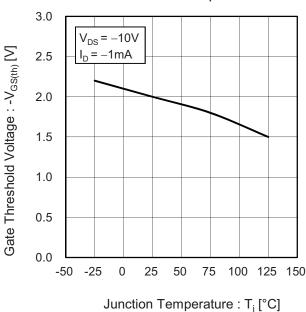
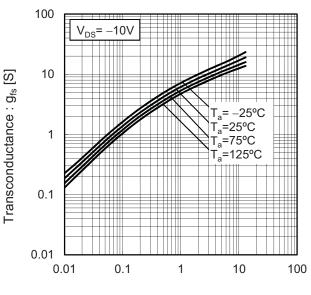


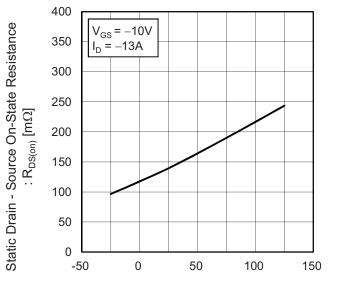
Fig.11 Transconductance vs. Drain Current



Drain Current : -I<sub>D</sub> [A]

Fig.12 Static Drain - Source On - State Fig.13 Static Drain - Source On - State Resistance vs. Gate Source Voltage Resistance vs. Drain Current(I) 400 1000 Static Drain - Source On-State Resistance T<sub>a</sub>=25°C Static Drain - Source On-State Resistance T<sub>2</sub>=25°C 350 V<sub>GS</sub>= -4.5V 300 -7.5A250  $:R_{DS(on)}$  [m $\Omega$ ] -13A  $:R_{DS(on)}\left[ m\Omega \right]$ 200 100 150 100 50 0 10 0 5 10 15 0.01 0.1 1 10 100 Gate - Source Voltage : -V<sub>GS</sub> [V] Drain Current : -I<sub>D</sub> [A]

Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



Resistance vs. Drain Current(II)

1000  $V_{GS} = -10V$   $T_a = 125^{\circ}C$   $T_a = 25^{\circ}C$   $T_a = -25^{\circ}C$   $T_a = -25^{\circ}C$   $T_a = -25^{\circ}C$   $T_a = 100$  0.01 0.01 100

Drain Current: -ID [A]

Fig.15 Static Drain - Source On - State

Fig.16 Static Drain - Source On - State
Resistance vs. Drain Current(III)

Toology

Ta=125°C

Ta=75°C

Ta=25°C

Ta=-25°C

Ta=-25°C

Ta=-25°C

Ta=-25°C

Ta=-25°C

Drain Current: -I<sub>D</sub> [A]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV) 1000 Static Drain - Source On-State Resistance =125°C \_=75°C \_=25°C -25°C  $:R_{DS(on)}\left[ m\Omega \right]$ 100 10 0.01 0.1 1 100 10 Drain Current: -ID [A]

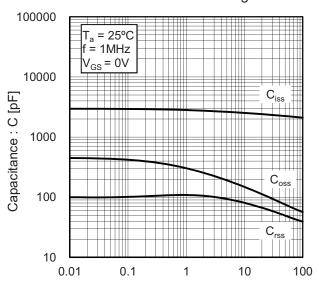
120 100 Drain Current Dissipation :  $I_D/I_D$  max. (%) 80 60 40 20 0 25 50 75 100 125 150 175 0

Fig.18 Drain Current Derating Curve



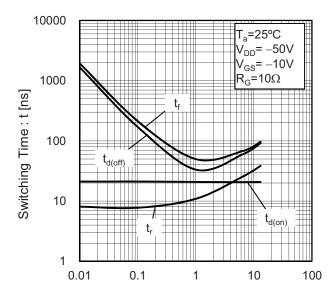
Junction Temperature : T<sub>i</sub> [°C]

Fig.19 Typical Capacitance vs. Drain - Source Voltage



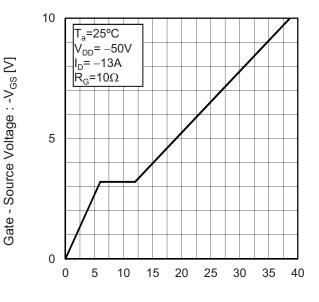
Drain - Source Voltage : -V<sub>DS</sub> [V]

Fig.20 Switching Characteristics



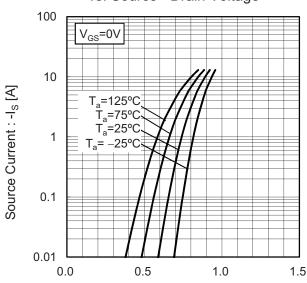
Drain Current: -I<sub>D</sub> [A]

Fig.21 Dynamic Input Characteristics



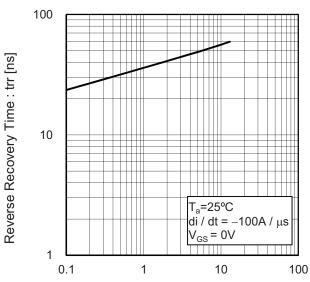
Total Gate Charge : Q<sub>g</sub> [nC]

Fig.22 Source Current vs. Source - Drain Voltage



Source-Drain Voltage : -V<sub>SD</sub> [V]





Source Current : -I<sub>S</sub> [A]

## Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

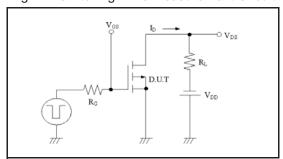


Fig.2-1 Gate Charge Measurement Circuit

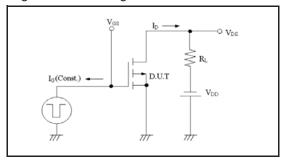


Fig.3-1 Avalanche Measurement Circuit

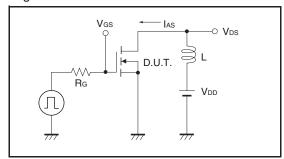


Fig.1-2 Switching Waveforms

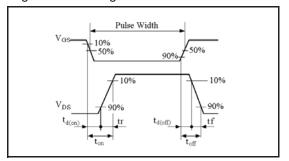


Fig.2-2 Gate Charge Waveform

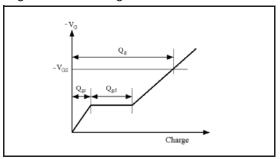
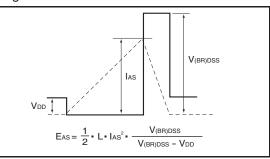
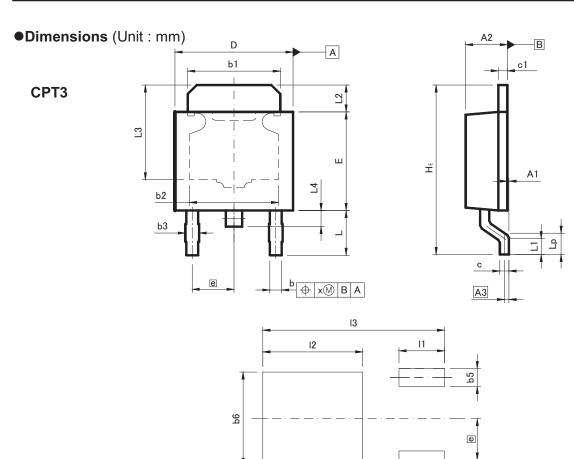


Fig.3-2 Avalanche Waveform





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
A1	0.00	0.15	0.000	0.006
A2	2.20	2.50	0.087	0.098
A3	0.	25	0.0	10
b	0.55	0.75	0.022	0.030
b1	5.00	5.30	0.197	0.209
b2	5.	00	0.1	97
b3	0.	75	0.0	30
С	0.40	0.60	0.016	0.024
c1	0.40	0.60	0.016	0.024
D	6.30	6.70	0.248	0.264
Е	5.40	5.80	0.213	0.228
е	2.	30	0.0	91
HE	9.00	10.00	0.354	0.394
L	2.20	2.80	0.087	0.110
L1	0.80	1.40	0.031	0.055
L2	1.20	1.80	0.047	0.071
L3	5.30		0.209	
L4	0.	90	0.0	35
Lp	1.00	1.60	0.039	0.063
X	_	0.25	_	0.010

DIM MILIME		ETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
b5	ı	1.00	ı	0.04
b6	1	5.20	-	0.205
11	_	2.50	_	0.098
12	_	5.50	_	0.217
13	-	10.00	-	0.394

Dimension in mm / inches

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JÁPAN	USA	EU	CHINA
CLASSⅢ	О 400 Ш	CLASS II b	CL ACCIII
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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